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Bib Data Sheet

**CONFIRMATION NO. 3321** 

RULE		LASS 257	GROUP ART UNIT 2815		TINL	ATTORNEY DOCKET NO. 04329.3137	
APPLICANTS  Kouji Matsuo, Yokohama-shi, JAPAN;  COPY FOR CIE							
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** FOREIGN APPLICATIONS ************************************							
IF REQUIRED, FOREIGN FILING LICENSE GRANTED ** 12/01/2003							
Foreign Priority claimed  yes no  35 USC 119 (a-d) conditions met yes no Met after Allowance  Verified and Acknowledged Examiner's Signature Initials			DR/	AWING	TOTAL CLAIMS 21		INDEPENDENT CLAIMS 2
arabow,							*
TITLE  Semiconductor device including metal insulator semiconductor field effect transistor and method of manufacturing the same							
LING FEE  FEES: Authority has been given in Paper Noto charge/credit DEPOSIT ACCOUNT ECEIVED Nofor following:				All Fees  1.16 Fees (Filing)  1.17 Fees (Processing Ext. of time)  1.18 Fees (Issue)  Other			
	kohama-shi, JAPAN;  IONS  10NS  1094 11/06/2002  N FILING LICENSE GRAI  INIT  INIT	RULE  kohama-shi, JAPAN;  DONE  10NS  1094 11/06/2002  N FILING LICENSE GRANTED  Wyes no Met after Allowance Initials  arabow,  cluding metal insulator semiconductor  to charge/credit DEPOSIT	RULE  Rohama-shi, JAPAN;  Nove Over  10NS  1094 11/06/2002  N FILING LICENSE GRANTED  STATE OR  COUNTRY  JAPAN  Cluding metal insulator semiconductor field effect trace:  Authority has been given in Paper  to charge/credit DEPOSIT ACCOUNT	RULE  Kohama-shi, JAPAN;  WONE ONE  10NS  10NS  1094 11/06/2002  N FILING LICENSE GRANTED  STATE OR SH  COUNTRY DRA  JAPAN  COUNTRY JAPAN  Cluding metal insulator semiconductor field effect transistor  Cluding metal insulator semiconductor field effect transistor  Cluding metal insulator semiconductor field effect transistor	RULE  Rohama-shi, JAPAN;  PONE QUE  NONS  1094 11/06/2002  N FILING LICENSE GRANTED  STATE OR SHEETS COUNTRY DRAWING 13  Cluding metal insulator semiconductor field effect transistor and method  All Fe  1.16 Fe  1.17 Fe  1.18 Fe	RULE  Kohama-shi, JAPAN;  POPE DIV  JONS  10NS  1094 11/06/2002  N FILING LICENSE GRANTED  STATE OR SHEETS TO: COUNTRY DRAWING CLA JAPAN  13  Cluding metal insulator semiconductor field effect transistor and method of metal country to charge/credit DEPOSIT ACCOUNT for following:    Authority has been given in Paper to charge/credit DEPOSIT ACCOUNT   1.18 Fees (Is)	RULE  Kohama-shi, JAPAN;  FILING LICENSE GRANTED  STATE OR SHEETS TOTAL COUNTRY DRAWING CLAIMS JAPAN 13  Cluding metal insulator semiconductor field effect transistor and method of manufacture to charge/credit DEPOSIT ACCOUNT  Authority has been given in Paper to charge/credit DEPOSIT ACCOUNT for following:    All Fees     1.16 Fees (Filing)       1.17 Fees (Processin   1.18 Fees (Issue)